

L Number	Hits	Search Text	DB	Time stamp
1	1	107006566	USPAT	2004/09/12 10:17
2	1	("6741114").PN.	USPAT	2004/09/12 10:17
3	19	ESD and conductivity and impurity and region and n-type and p-type and insulating and source and drain and metal and polysilicon and oxide and gate and electrode and input and output and contact and hole	USPAT	2004/09/12 10:23
4	15	ESD and conductivity and impurity and region and n-type and p-type and dielectric and source and drain and metal and polysilicon and oxide and gate and electrode and input and output and contact and hole	USPAT	2004/09/12 10:19
5	14	ESD and conductivity and impurity and region and n-type and p-type and insulating and source and drain and metal and polysilicon and oxide and gate and electrode and input and output and contact and hole and dielectric	USPAT	2004/09/12 10:23
6	15	ESD and conductivity and impurity and region and n-type and p-type and insulating and source and drain and metal and polysilicon and oxide and gate and electrode and input and output and contact and dielectric	USPAT	2004/09/12 10:23
7	1	("5985722").PN.	USPAT	2004/09/12 10:24
8	1	((("5985722").PN.) and (capacitance or capcitor or active or area or polysilicon or isolation or entire or structure or oxide or metal or barrier or first or second or insulating or dielectric or conductivity)	USPAT	2004/09/12 10:35
9	1401	438/197	USPAT	2004/09/12 10:35
10	1774	438/239	USPAT	2004/09/12 10:35
11	495	438/294	USPAT	2004/09/12 10:35
12	178	438/295	USPAT	2004/09/12 10:35
13	1111	438/296	USPAT	2004/09/12 10:35
14	819	438/297	USPAT	2004/09/12 10:35
15	178	438/353	USPAT	2004/09/12 10:35
16	271	438/359	USPAT	2004/09/12 10:35
17	200	438/362	USPAT	2004/09/12 10:36
18	1145	438/381	USPAT	2004/09/12 10:36
19	174	438/583	USPAT	2004/09/12 10:36
20	422	438/647	USPAT	2004/09/12 10:36
21	807	438/649	USPAT	2004/09/12 10:36

9/12/04